

AP3408

General Description

The AP3408 is a current mode, PWM synchronous buck DC/DC converter, capable of driving a 2A load with high efficiency, excellent line and load regulation. It operates in continuous PWM mode.

The AP3408 integrates synchronous P-channel and N-channel power MOSFET switches with low on-resistance. It is ideal for portable applications powered from a single Li-ion battery. 100% duty cycle and low on-resistance P-channel internal power MOSFET can maximize the battery life.

The switching frequency of AP3408 can be programmable from 300kHz to 4MHz, which allows small-sized components, such as capacitors and inductors A standard series of inductors from several different manufacturers are available. This feature greatly simplifies the design of switch-mode power supplies.

The AP3408 is available in DFN-3×3-10 and PSOP-8 packages.

Features

- Input Voltage Range: 2.6 to 5.5V
- Adjustable Output from 0.8 to 5V
- 0.8V Reference Voltage with ± 2% Precision
- Output Current: 2A
- High Efficiency up to 95%
- Low R_{DSON} Internal Switches
- Programmable Frequency: 300kHz to 4MHz
- Current Mode Control
- Forced Continuous-mode Operation
- 100% Duty Cycle
- Synchronizable Switching Frequency
- Power Good Output Voltage Monitoring
- Built-in Soft-start
- Built-in Short Circuit Protection
- Built-in Thermal Shutdown Protection
- Built-in Current Limit Function

Applications

- Portable Media Player
- Digital Still and Video Cameras
- Notebook

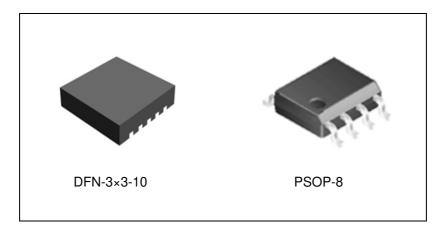


Figure 1. Package Types of AP3408



AP3408

Pin Configuration

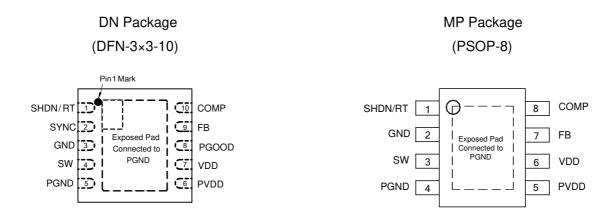


Figure 2. Pin Configuration of AP3408 (Top View)

Pin Description

Pin Number		Pin Name	Description		
DFN-3×3-10	PSOP-8	Pin Name	Description		
1	1	SHDN/RT	Oscillator resistor input. Connect a resistor to GND from this pin to set the switching frequency. Forcing this pin to $V_{\rm DD}$ to shutdown the device		
2		SYNC	External clock synchronization input. The oscillation frequency can be synchronized to an external oscillation applied to this pin. When tied to VDD, the internal oscillator is selected		
3	2	GND	Signal ground. All small-signal ground, such as the compensation components and the exposed pad should be connected to this pin, which in turn connects to PGND at one point		
4	3	SW	Internal power switch output. Connect this pin with one terminal of the inductor		
5	4	PGND	Power ground. Connect this pin as close as possible to CIN and COUT		
6	5	PVDD	Power input supply. Decouple this pin to PGND with a capacitor		
7	6	VDD	Signal input supply. Decouple this pin to GND with a capacitor. Normally $V_{\rm DD}$ is equal to $V_{\rm PVDD}$		
8		PGOOD	Power Good Indicator. Open-drain logic output that is pulled to ground when the output voltage is not within \pm 12.5% of regulation point		
9	7	FB	Feedback voltage. This pin is the inverting input of internal error amplifier. It senses the converter output voltage through an external resistor divider. The internal reference voltage is 0.8V, which determines the output voltage through the resistor divider		
10	8	COMP	Compensation input. This pin is the output of internal error amplifier. Connect external compensation elements to this pin to stabilize the control loop		



AP3408

Functional Block Diagram

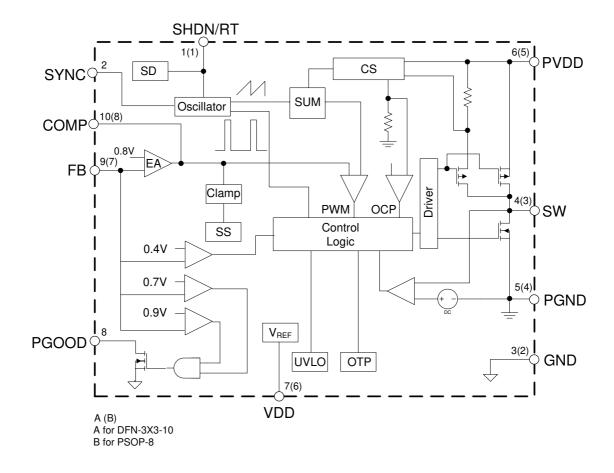
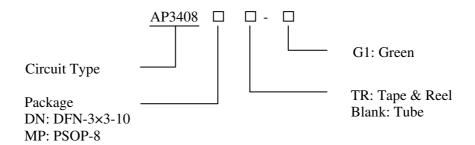


Figure 3. Functional Block Diagram of AP3408



AP3408

Ordering Information



Package	Temperature Range	Part Number Green	Marking ID Green	Packing Type
DFN-3×3-10		AP3408DNTR-G1	BFA	Tape & Reel
PSOP-8	-40 to 125°C	AP3408MP-G1	3408MP-G1	Tube
P30P-8		AP3408MPTR-G1	3408MP-G1	Tape & Reel

BCD Semiconductor's Pb-free products, as designated with "G1" suffix in the part number, are RoHS compliant and green.

Absolute Maximum Ratings (Note 1)

Parameter		Symbol	Value	Unit
VDD Pin Voltage		$V_{ m DD}$	-0.3 to 6	V
PVDD Pin Voltage		V_{PVDD}	-0.3 to 6	V
FB Pin Voltage		$ m V_{FB}$	-0.3 to 6	V
COMP Pin Voltage		V_{COMP}	-0.3 to 6	V
SW Pin Voltage		V_{SW}	-0.3 to V _{IN} +0.3	V
SHDN/RT Pin Voltage		V _{SHDN/RT}	-0.3 to 6	V
Thermal Resistance	mal Resistance DFN-3×3-10 PSOP-8		110 75	°C/W
Operating Junction Temperature		T _J	150	°C
Storage Temperature		T_{STG}	-65 to 150	°C
Lead Temperature (Soldering, 10 sec)		$T_{ m LEAD}$	260	°C
ESD (Machine Model)			200	V
ESD (Human Body Model)			2000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.



AP3408

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Input Voltage	$V_{\rm IN}$	2.6	5.5	V
Maximum Output Current	I _{OUT (MAX)}	2		A
Operating Junction Temperature	$T_{\rm J}$	-40	125	°C

Electrical Characteristics

 $V_{\text{IN}}\!\!=\!\!V_{\text{DD}}\!\!=\!\!3.3V,\,T_{A}\!\!=\!\!25\,^{\circ}\!\text{C}$, unless otherwise specified.

Parameters	Symbol	Conditions	Min	Тур	Max	Unit	
INPUT SECTION							
Input Voltage Range	V_{DD}		2.6		5.5	V	
Supply Current	I_Q	V _{FB} =0.75V, No Switching		460		μΑ	
Shutdown Supply Current	I _{SHDN}	Shutdown, V _{IN} =5.5V			1	μΑ	
Under Voltage Threshold Lockout	V _{UVLO}	V _{DD} Rising		2.2		V	
Under Voltage Hysteresis Lockout	V _{HUVLO}			300		mV	
FEEDBACK SECTION							
Feedback Voltage	V_{FB}		0.784	0.8	0.816	V	
FB Pin Bias Current	I_{FB}			0.1	0.4	μΑ	
Current Sense Transresistance	R_{T}			0.2		Ω	
Switching Leakage Current		V _{SHDN/RT} =V _{IN} =5.5V			1	μΑ	
Error Gain Amplifier Voltage	G_{V}			800			
Error Amplifier Trans-conductance	G_{S}			800		μA /V	



AP3408

Electrical Characteristics (Continued)

 $V_{\text{IN}}\!\!=\!\!V_{\text{DD}}\!\!=\!\!3.3V,\,T_{\text{A}}\!\!=\!\!25\,^{\circ}\!\text{C}$, unless otherwise specified.

Parameters	Symbol	Conditions	Min	Тур	Max	Unit	
OSCILLATOR SECTION							
RT Pin Voltage	V_{RT}			0.8		V	
Switching Eraguanay	f_{OSC}	R_{OSC} =330k Ω	0.8	1	1.2	MHz	
Switching Frequency		ADJ Frequency	0.3		4	MHz	
Maximum Duty Cycle	D_{MAX}	$V_{FB} = 0.75V$	100			%	
POWER SWITCH SECTI	ON						
Switch Current Limit	I _{LIMIT}	V _{FB} =0.75V	2.2	3.8		A	
Internal P-FET On Resistance	R _{PDSON}	I _{SW} =500mA		0.11	0.16	Ω	
Internal N-FET On Resistance	R _{NDSON}	I _{SW} =-500mA		0.11	0.17	Ω	
SHDN/RT SECTION							
Shutdown Threshold				V _{DD} -0.7	$V_{\rm DD}$ -0.4	V	
PGOOD SECTION							
PGOOD Voltage Range				±12.5	±15	%	
PGOOD Pull Down Resistance					120	Ω	
TOTAL DEVICE							
Output Current	I_{OUT}	V_{DD} =2.6 to 5.5V V_{OUT} =2.5V	2			A	
Output Voltage Line Regulation	LNR	V_{DD} =2.7 to 5.5V I_{OUT} =100mA		0.4		%/V	
Output Voltage Load Regulation	LOD	I _{OUT} =0.01 to 2A		±0.2		%	
Soft-start Time	t_{SS}	$I_{OUT}=10mA$		1.5		ms	
Thermal Shutdown Temperature	T_{OTSD}			160		°C	
Thermal Shutdown Temperature Hysteresis	T_{HYS}			20		℃	



AP3408

Typical Performance Characteristics

 $V_{IN}=V_{DD}=V_{PVDD}=3.3V, T_A=25^{\circ}C$, unless otherwise specified.

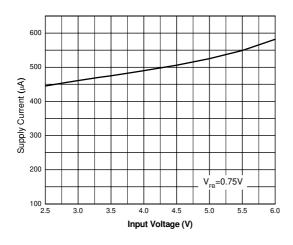


Figure 4. Supply Current vs. Input Voltage

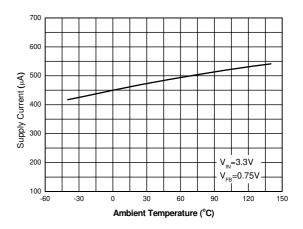


Figure 5. Supply Current vs. Ambient Temperature

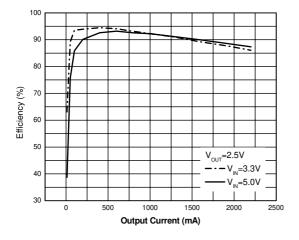


Figure 6. Efficiency vs. Output Current

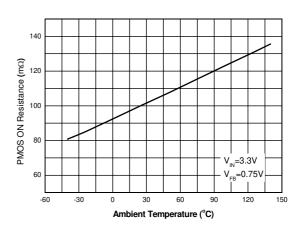


Figure 7. PMOS ON Resistance vs. Ambient Temperature



AP3408

Typical Performance Characteristics (Continued)

 $V_{IN}=V_{DD}=V_{PVDD}=3.3V, T_A=25^{\circ}C$, unless otherwise specified.

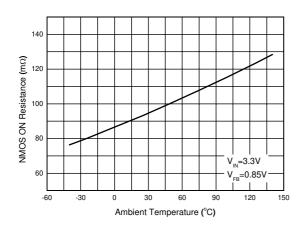
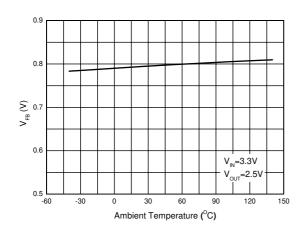


Figure 8. NMOS ON Resistance vs. Ambient Temperature

Figure 9. Frequency vs. Ambient Temperature



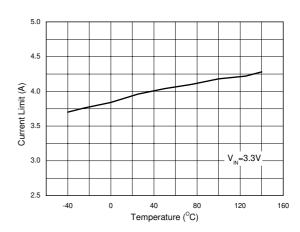


Figure 10. V_{FB} vs. Ambient Temperature

Figure 11. Current Limit vs. Ambient Temperature



AP3408

Typical Application

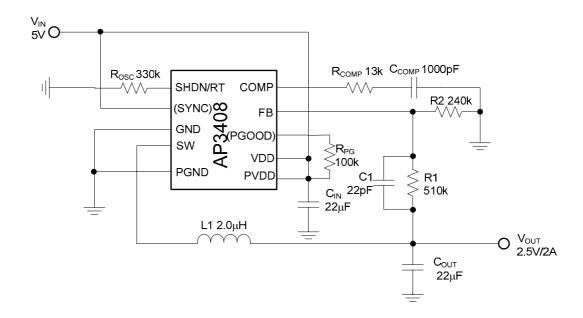


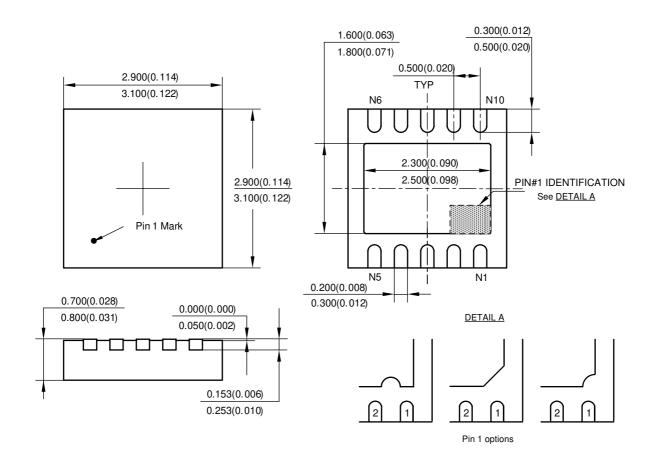
Figure 12. Typical Application of AP3408



AP3408

Mechanical Dimensions

DFN-3×3-10 Unit: mm(inch)

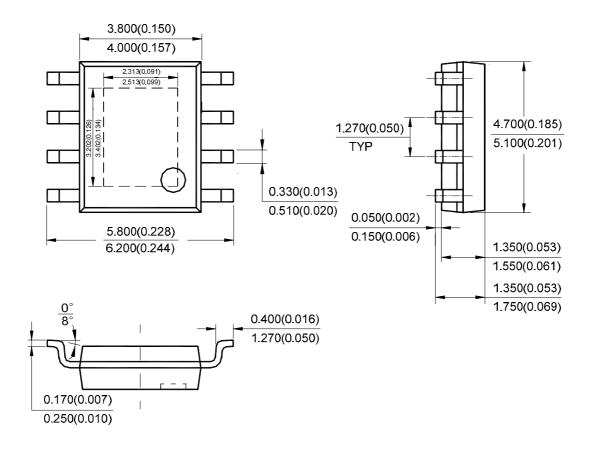




AP3408

Mechanical Dimensions (Continued)

PSOP-8 Unit: mm(inch)



Note: Eject hole, oriented hole and mold mark is optional.





BCD Semiconductor Manufacturing Limited

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